

제20회 한국반도체학술대회

2013년 2월 4일(월)~6일(수) / 웰리힐리파크 (구, 성우리조트)

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G. Device & Process Modeling, Simulation and Reliability 분과

Room H

난실 (본관, 5층)

2013년 2월 6일(수) 09:40-10:55

[WH1-G] Device Simulation

좌장: 박찬형(광운대학교), 조인욱(SK 하이닉스)

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| WH1-G-1 | 09:40-09:55 | Si:P Nanowire as Next-Generation Interconnect for Ultra-Scale Devices: Investigation of Metallic Properties with a Tight-Binding Approach
Hoon Ryu ¹ , Sunhee Lee ² , and Gerhard Klimeck ³
¹ Supercomputing Center, Korea Institute of Science and Technology Information, ² Samsung Advanced Institute of Technology, ³ Network for Computational Nanoelectronics, Purdue University |
| WH1-G-2 | 09:55-10:10 | Quantum Simulation of P-Type Nanowire Schottky Barrier MOSFETs: Silicon Versus Germanium Channel
Jaehyun Lee, Wonchul Choi, and Mincheol Shin
Department of Electrical Engineering, KAIST |
| WH1-G-3 | 10:10-10:25 | Surface Roughness Effects in Schottky Barrier Tunneling Transistors : Comparative Study against Ohmic Contact Devices
Hyo-Eun Jung and Mincheol Shin
Department of Electrical Engineering, KAIST |
| WH1-G-4 | 10:25-10:40 | Computational Study of P-Type Germanium Nanowire Field Effect Transistors
Ju-Young Jung ¹ , Hoon Ryu ² , and Mincheol Shin ¹
¹ Department of Electrical Engineering, KAIST, ² Supercomputing Center, Korea Institute Science and Technology Information |
| WH1-G-5 | 10:40-10:55 | Enhanced Photoresponse of Plasmonic Terahertz Wave Detector based on Silicon Field Effect Transistors with Asymmetric Source and Drain Structures
Min Woo Ryu, Sung-Ho Kim, and Kyung Rok Kim
School of Electrical and Computer Engineering, Ulsan National Institute of Science and Technology |